

SN74CBTLV3257 低电压、4 位、2 选 1 FET 多路复用器/多路解复用器

1 特性

- 两个端口间使用 5Ω 开关连接
- 数据 I/O 端口上的轨至轨开关
- I_{off} 支持局部关断模式运行
- 闩锁性能超出 JESD 78 II 类规范要求的 100mA
- 静电放电 (ESD) 保护性能超过 JESD 22 规范的要求
 - 2000V 人体放电模型 (A114-A)
 - 200V 机器模型 (A115-A)

2 应用范围

- 物联网
- 无线耳机
- 电视机
- 4 位总线多路复用和多路解复用

3 说明

SN74CBTLV3257 器件是一款 4 位 2 选 1 高速 FET 多路复用器/多路解复用器。此开关具有低通态电阻，可以在最短传播延迟情况下建立连接。

选择 (S) 输入控制数据流。当输出使能 ($\overline{OE}$) 输入为高电平时，FET 多路复用器/多路解复用器被禁用。

该器件完全适用于使用 I_{off} 的局部掉电应用。 I_{off} 特性确保在关断时防止损坏电流通过器件回流。该器件可在关断时提供隔离。

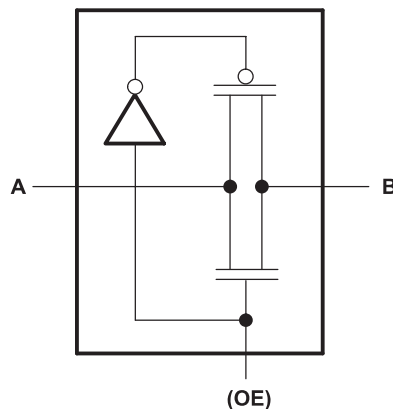
为了确保加电或断电期间的高阻抗状态， $\overline{OE}$ 应通过一个上拉电阻器被连接至 V_{CC} ；该电阻器的最小值由驱动器的电流吸入能力来决定。

器件信息⁽¹⁾

器件型号	封装	封装尺寸 (标称值)
SN74CBTLV3257DBQ	SSOP (16)	4.90mm × 3.90mm
SN74CBTLV3257PW	TSSOP (16)	5.00mm × 4.40mm
SN74CBTLV3257DGV	TVSOP (16)	3.60mm × 4.40mm
SN74CBTLV3257D	SOIC (16)	9.90mm × 3.91mm
SN74CBTLV3257RGY	VQFN (16)	4.00mm × 3.50mm
SN74CBTLV3257RSV	UQFN (16)	2.60mm × 1.80mm

(1) 如需了解所有可用封装，请参阅产品说明书末尾的可订购产品附录。

简化原理图 (每个 FET 开关)



目录

1	特性	1	8.4	Device Functional Modes.....	8
2	应用范围	1	9	Application and Implementation	9
3	说明	1	9.1	Application Information.....	9
4	修订历史记录	2	9.2	Typical Application	9
5	Pin Configuration and Functions	3	10	Power Supply Recommendations	10
6	Specifications	5	11	Layout	11
6.1	Absolute Maximum Ratings	5	11.1	Layout Guidelines	11
6.2	ESD Ratings.....	5	11.2	Layout Example	11
6.3	Recommended Operating Conditions.....	5	12	器件和文档支持	12
6.4	Thermal Information	5	12.1	文档支持	12
6.5	Electrical Characteristics.....	6	12.2	接收文档更新通知	12
6.6	Switching Characteristics	6	12.3	社区资源.....	12
7	Parameter Measurement Information	7	12.4	商标.....	12
8	Detailed Description	8	12.5	静电放电警告	12
8.1	Overview	8	12.6	术语表	12
8.2	Functional Block Diagram	8	13	机械、封装和可订购信息	12
8.3	Feature Description.....	8			

4 修订历史记录

注：之前版本的页码可能与当前版本有所不同。

Changes from Revision L (October 2016) to Revision M	Page
• Changed the pin images appearance	3
• Changed the <i>Thermal Information</i> table	5

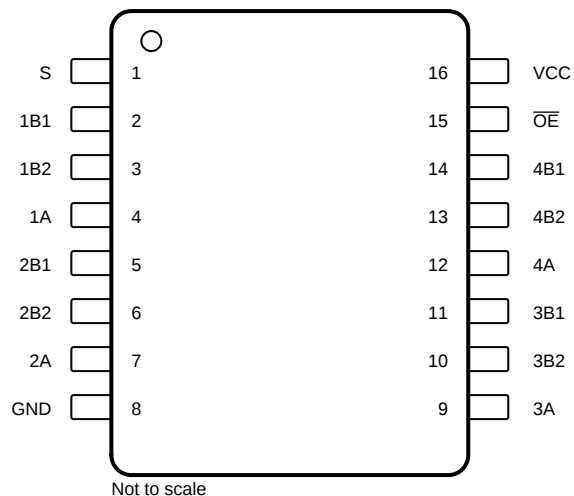
Changes from Revision K (April 2015) to Revision L	Page
• 已添加 将 TSSOP (16) 添加到器件信息 表.....	1
• Added Junction temperature, T_J in <i>Absolute Maximum Ratings</i>	5
• Changed wording in <i>Detailed Design Procedure</i> to clarify device operation	10
• 已添加 添加了接收文档更新通知 部分和社区资源 部分	12

Changes from Revision J (December 2012) to Revision K	Page
• 删除了 订购信息 表，请参阅 机械、封装和可订购信息	1
• 已添加 引脚配置和功能 部分，ESD 额定值 表，特性 说明 部分、器件功能模式、应用和实施 部分、电源相关建议 部分、布局 部分、器件和文档支持 部分以及机械、封装和可订购信息 部分	1
• 已添加 应用.....	1
• 已添加 器件信息 表。	1

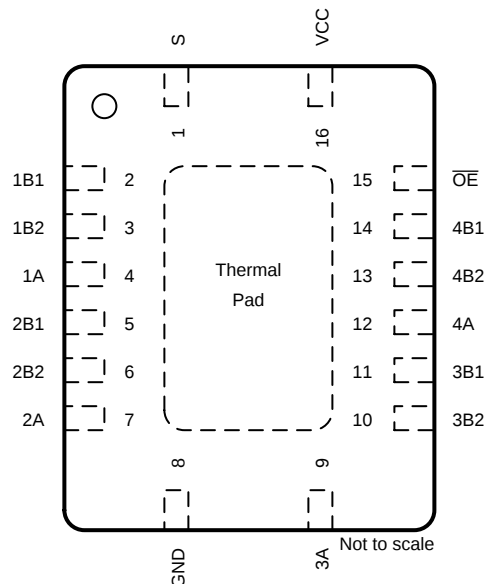
Changes from Revision I (October 2003) to Revision J	Page
• 添加了 QFN 订购信息和封装引脚布局.....	1

5 Pin Configuration and Functions

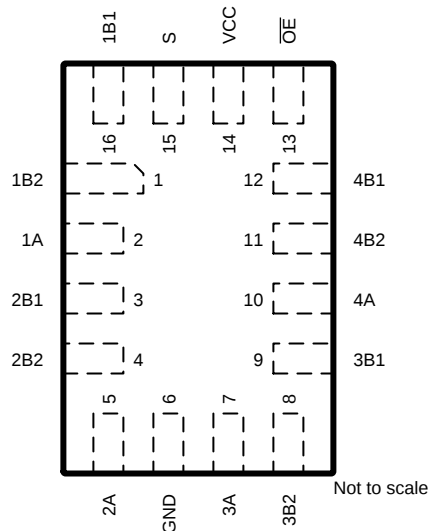
D, DBQ, DGV, and PW Package
16-Pin SOIC, SSOP, TVSOP, and TSSOP
(Top View)



RGY Package
16-Pin VQFN
(Top View)



RSV Package
16-Pin UQFN
(Top View)



SN74CBTLV3257

ZHCSIJ4M – DECEMBER 1997 – REVISED JULY 2018

www.ti.com.cn
Pin Functions

PIN			I/O	DESCRIPTION
NAME	SOIC, SSOP, TVSOP, TSSOP, VQFN	UQFN		
1A	4	2	I/O	Channel 1 out/in common
1B1	2	16	I/O	Channel 1 in/out 1
1B2	3	1	I/O	Channel 1 in/out 2
2A	7	5	I/O	Channel 2 out/in common
2B1	5	3	I/O	Channel 2 in/out 1
2B2	6	4	I/O	Channel 2 in/out 2
3A	9	7	I/O	Channel 3 out/in common
3B1	11	9	I/O	Channel 3 in/out 1
3B2	10	8	I/O	Channel 3 in/out 2
4A	12	10	I/O	Channel 4 out/in common
4B1	14	12	I/O	Channel 4 in/out 1
4B2	13	11	I/O	Channel 4 in/out 2
GND	8	6	—	Ground
$\overline{OE}$	15	13	I	Output Enable, active low
S	1	15	I	Select
V _{CC}	16	14	—	Power

6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)⁽¹⁾

		MIN	MAX	UNIT
V _{CC}	Supply voltage	–0.5	4.6	V
V _I	Input voltage ⁽²⁾	–0.5	4.6	V
	Continuous channel current		128	mA
I _{IK}	Input clamp current	V _{I/O} < 0	–50	mA
T _J	Junction temperature		150	°C
T _{stg}	Storage temperature	–65	150	°C

- Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

6.2 ESD Ratings

			VALUE	UNIT
V _(ESD)	Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	2000	V

- JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)⁽¹⁾

		MIN	MAX	UNIT
V _{CC}	Supply voltage	2.3	3.6	V
V _{IH}	High-level control input voltage	V _{CC} = 2.3 V to 2.7 V	1.7	V
		V _{CC} = 2.7 V to 3.6 V	2	
V _{IL}	Low-level control input voltage	V _{CC} = 2.3 V to 2.7 V	0.7	V
		V _{CC} = 2.7 V to 3.6 V	0.8	
T _A	Operating free-air temperature	–40	85	°C

- All unused control inputs of the device must be held at V_{CC} or GND to ensure proper device operation. See [Implications of Slow or Floating CMOS Inputs](#) SCBA004.

6.4 Thermal Information

THERMAL METRIC ⁽¹⁾		SN74CBTLV3257					UNIT
		D	DBQ	DGV	PW	RGY	
		16 PINS	16 PINS	16 PINS	16 PINS	16 PINS	
R _{θJA}	Junction-to-ambient thermal resistance	86.7	112.4	123.1	110.9	43.8	°C/W
R _{θJC(top)}	Junction-to-case (top) thermal resistance	47.8	63.6	48.7	45.8	57.2	°C/W
R _{θJB}	Junction-to-board thermal resistance	43.7	54.8	54.9	56.0	21.4	°C/W
ψ _{JT}	Junction-to-top characterization parameter	12.3	17.0	5.2	5.4	1.7	°C/W
ψ _{JB}	Junction to board characterization parameter	43.5	54.4	54.3	55.4	21.5	°C/W
R _{θJC(botto m}	Junction-to-case (bottom) thermal resistance	-	-	-	-	9.7	°C/W

- For more information about traditional and new thermal metrics, see the [Semiconductor and IC Package Thermal Metrics](#) application report.

6.5 Electrical Characteristics

over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		MIN	TYP ⁽¹⁾	MAX	UNIT
V_{IK}		$V_{CC} = 3\text{ V}$,	$I_I = -18\text{ mA}$			-1.2	V
I_I		$V_{CC} = 3.6\text{ V}$,	$V_I = V_{CC}$ or GND			±1	μA
I_{off}		$V_{CC} = 0$,	V_I or $V_O = 0$ to 3.6 V			15	μA
I_{CC}		$V_{CC} = 3.6\text{ V}$,	$I_O = 0$, $V_I = V_{CC}$ or GND			10	μA
$\Delta I_{CC}^{(2)}$	Control inputs	$V_{CC} = 3.6\text{ V}$,	One input at 3 V, Other inputs at V_{CC} or GND			300	μA
C_i		$V_I = 3\text{ V}$ or 0			3		pF
$C_{io(OFF)}$	A port	$V_O = 3\text{ V}$ or 0, $\overline{OE} = V_{CC}$			10.5		pF
	B port				5.5		
$r_{on}^{(3)}$	$V_{CC} = 2.3\text{ V}$, TYP at $V_{CC} = 2.5\text{ V}$	$V_I = 0$	$I_I = 64\text{ mA}$		5	8	Ω
			$I_I = 24\text{ mA}$		5	8	
		$V_I = 1.7\text{ V}$	$I_I = 15\text{ mA}$		27	40	
	$V_{CC} = 3\text{ V}$	$V_I = 0$	$I_I = 64\text{ mA}$		5	7	
			$I_I = 24\text{ mA}$		5	7	
		$V_I = 2.4\text{ V}$	$I_I = 15\text{ mA}$		10	15	

 (1) All typical values are at $V_{CC} = 3.3\text{ V}$ (unless otherwise noted), $T_A = 25^\circ\text{C}$.

 (2) This is the increase in supply current for each input that is at the specified voltage level, rather than V_{CC} or GND.

(3) Measured by the voltage drop between the A and the B terminals at the indicated current through the switch. On-state resistance is determined by the lower of the voltages of the two (A or B) terminals.

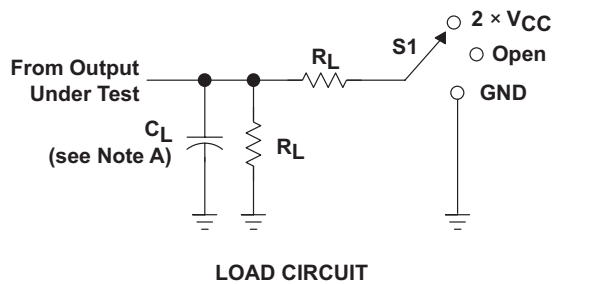
6.6 Switching Characteristics

over recommended operating free-air temperature range (unless otherwise noted) (See Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	$V_{CC} = 2.5 \pm 0.2\text{ V}$		$V_{CC} = 3.3\text{ V} \pm 0.3\text{ V}$		UNIT
			MIN	MAX	MIN	MAX	
t_{pd}	A or B ⁽¹⁾	B or A		0.15		0.25	ns
	S	A or B	1.8	6.1	1.8	5.3	
t_{en}	S	A or B	1.7	6.1	1.7	5.3	ns
t_{dis}	S	A or B	1	4.8	1	4.5	ns
t_{en}	$\overline{OE}$	A or B	1.9	5.6	2	5	ns
t_{dis}	$\overline{OE}$	A or B	1	5.5	1.6	5.5	ns

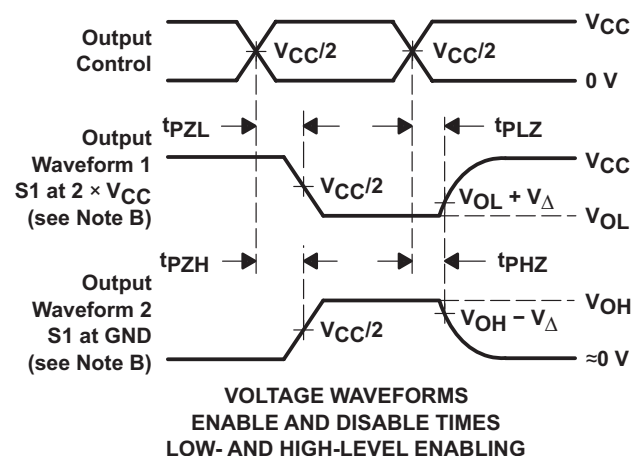
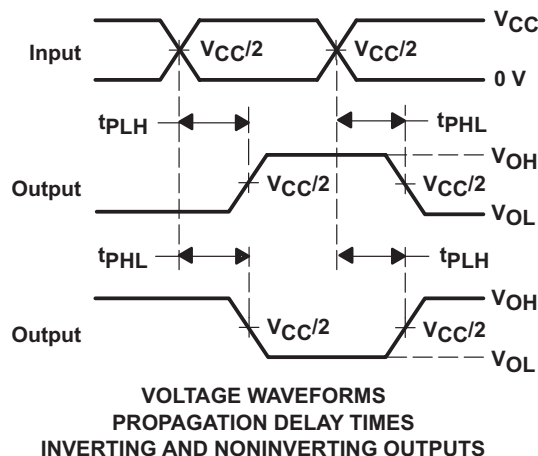
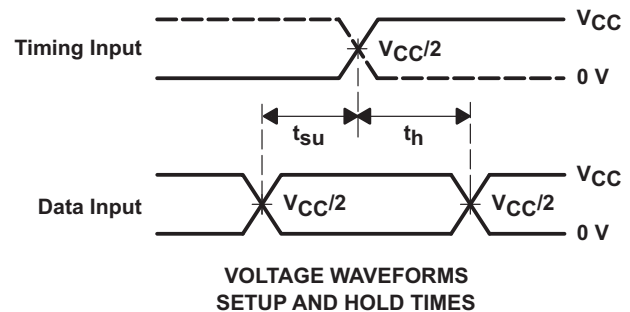
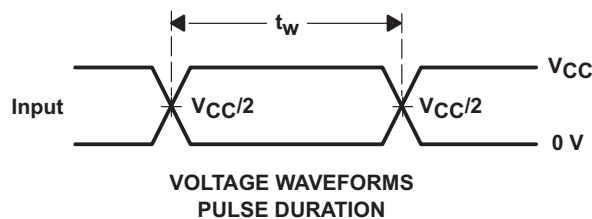
(1) The propagation delay is the calculated RC time constant of the typical on-state resistance of the switch and the specified load capacitance, when driven by an ideal voltage source (zero output impedance).

7 Parameter Measurement Information



TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	$2 \times V_{CC}$
t_{PHZ}/t_{PZH}	GND

V_{CC}	C_L	R_L	V_{Δ}
$2.5 \text{ V} \pm 0.2 \text{ V}$	30 pF	500 Ω	0.15 V
$3.3 \text{ V} \pm 0.3 \text{ V}$	50 pF	500 Ω	0.3 V



- NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR $\leq 10 \text{ MHz}$, $Z_O = 50 \Omega$, $t_r \leq 2 \text{ ns}$, $t_f \leq 2 \text{ ns}$.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis} .
F. t_{PZL} and t_{PZH} are the same as t_{en} .
G. t_{PLH} and t_{PHL} are the same as t_{pd} .
H. All parameters and waveforms are not applicable to all devices.

Figure 1. Load Circuit and Voltage Waveforms

8 Detailed Description

8.1 Overview

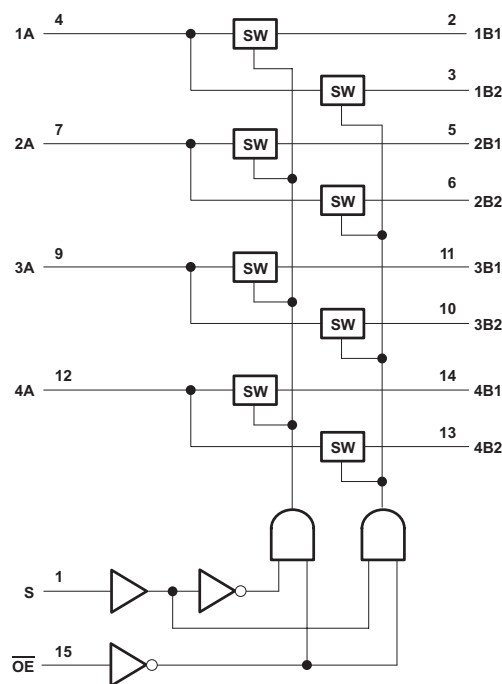
The SN74CBTLV3257 device is a 4-bit 1-of-2 high-speed FET multiplexer and demultiplexer. The low ON-state resistance of the switch allows connections to be made with minimal propagation delay.

The select (S) input controls the data flow. The FET multiplexers and demultiplexers are disabled when the output-enable ($\overline{\text{OE}}$) input is high.

This device is fully specified for partial-power-down applications using I_{off} . The I_{off} feature ensures that damaging current will not backflow through the device when it is powered down. The device has isolation during power off.

To ensure the high-impedance state during power up or power down, $\overline{\text{OE}}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

8.2 Functional Block Diagram



8.3 Feature Description

The SN74CBTLV3257 features 5- Ω switch connection between ports, allowing for low signal loss across the switch. Rail-to-rail switching on data I/O allows for full voltage swing outputs. I_{off} supports partial-power-down mode operation, protecting the chip from voltages at output ports when it is not powered on. Latch-up performance exceeds 100 mA per JESD 78, Class II.

8.4 Device Functional Modes

Table 1 shows the functional modes of SN74CBTLV3257.

Table 1. Function Table

INPUTS		FUNCTION
$\overline{\text{OE}}$	S	
L	L	A port = B1 port
L	H	A port = B2 port
H	X	Disconnect

9 Application and Implementation

NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

9.1 Application Information

The SN74CBTLV3257 can be used to multiplex and demultiplex up to 4 channels simultaneously in a 2:1 configuration. The application shown here is a 4-bit bus being multiplexed between two devices. the $\overline{OE}$ and S pins are used to control the chip from the bus controller. This is a very generic example, and could apply to many situations. If an application requires less than 4 bits, be sure to tie the A side to either high or low on unused channels.

9.2 Typical Application

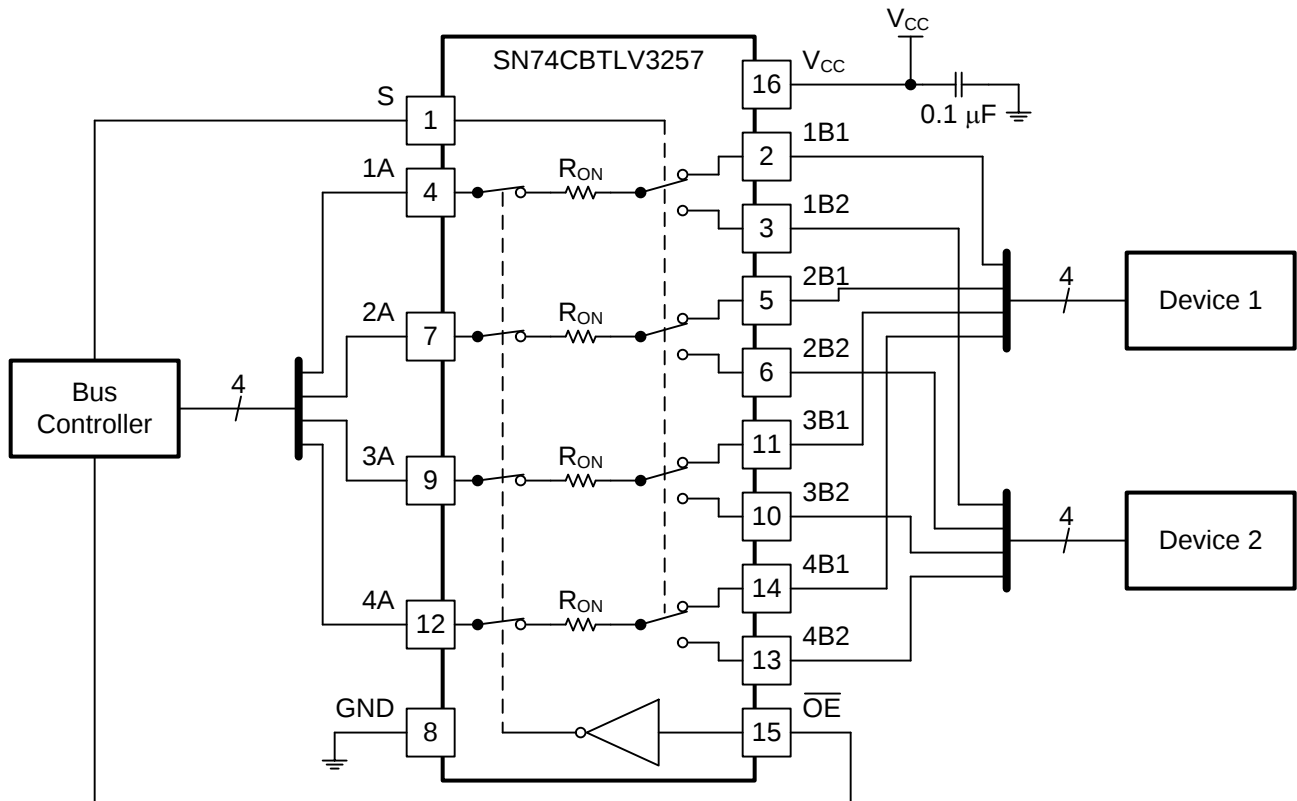


Figure 2. Typical Application of the SN74CBTLV3257

9.2.1 Design Requirements

- Recommended Input Conditions:
 - For specified high and low levels, see V_{IH} and V_{IL} in [Recommended Operating Conditions](#).
 - Inputs and outputs are overvoltage tolerant slowing them to go as high as 4.6 V at any valid V_{CC} .
- Recommended Output Conditions:
 - Load currents should not exceed ± 128 mA per channel.
- Frequency Selection Criterion:
 - Maximum frequency tested is 200 MHz.

Typical Application (continued)

- Added trace resistance/capacitance can reduce maximum frequency capability; use layout practices as directed in [Layout](#).

9.2.2 Detailed Design Procedure

The 4-bit bus is connected directly to the 1A, 2A, 3A, and 4A ports (known as the xA port) on the SN74CBTLV3257, which essentially splits it into two busses, coming out of the xB1 and xB2 ports. When S is high, xB2 is the active bus, and when S is low, xB1 is the active bus. This means that Device 2 is connected to the bus controller when S is high, and Device 1 is connected to the bus controller when S is low. This setup is especially useful when two devices are hard coded with the same address and only one bus is available. The $\overline{OE}$ connection can be used to disconnect all devices from the bus controller if necessary.

The 0.1- μ F capacitor on V_{CC} is a decoupling capacitor and should be placed as close as possible to the device.

9.2.3 Application Curve

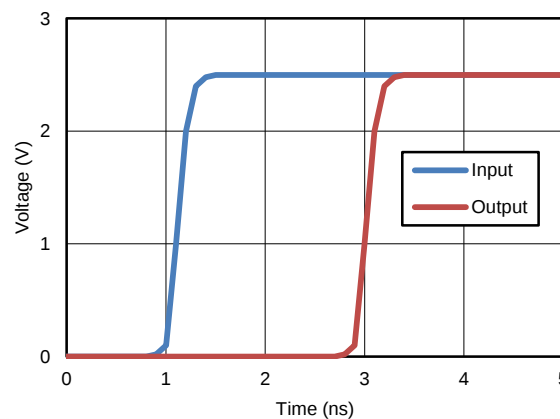


Figure 3. Propagation Delay (t_{pd}) Simulation Result at $V_{CC} = 2.5$ V

10 Power Supply Recommendations

The power supply can be any voltage between the minimum and maximum supply voltage rating listed in the [Recommended Operating Conditions](#) table.

Each V_{CC} terminal should have a good bypass capacitor to prevent power disturbance. For devices with a single supply, a 0.1- μ F bypass capacitor is recommended. If multiple pins are labeled V_{CC} , then a 0.01- μ F or 0.022- μ F capacitor is recommended for each V_{CC} because the V_{CC} pins are tied together internally. For devices with dual-supply pins operating at different voltages, for example V_{CC} and V_{DD} , a 0.1- μ F bypass capacitor is recommended for each supply pin. To reject different frequencies of noise, use multiple bypass capacitors in parallel. Capacitors with values of 0.1 μ F and 1 μ F are commonly used in parallel. The bypass capacitor should be installed as close to the power terminal as possible for best results.

11 Layout

11.1 Layout Guidelines

Reflections and matching are closely related to the loop antenna theory but are different enough to be discussed separately from the theory. When a PCB trace turns a corner at a 90° angle, a reflection can occur. A reflection occurs primarily because of the change of width of the trace. At the apex of the turn, the trace width increases to 1.414 times the width. This increase upsets the transmission-line characteristics, especially the distributed capacitance and self-inductance of the trace which results in the reflection. Not all PCB traces can be straight and therefore some traces must turn corners. [Figure 4](#) shows progressively better techniques of rounding corners. Only the last example (BEST) maintains constant trace width and minimizes reflections.

11.2 Layout Example

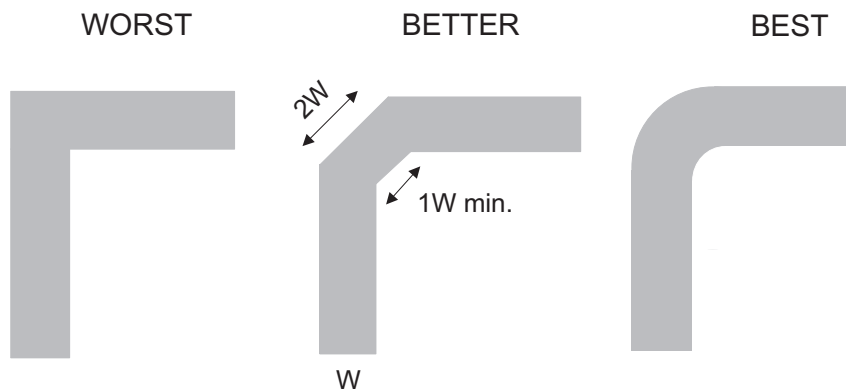


Figure 4. Trace Example

12 器件和文档支持

12.1 文档支持

12.1.1 相关文档

请参阅如下相关文档：

- 《慢速或浮点 CMOS 输入的影响》，SCBA004
- 《选择合适的德州仪器 (TI) 信号开关》，SZZA030

12.2 接收文档更新通知

要接收文档更新通知，请导航至 TI.com.cn 上的器件产品文件夹。单击右上角的通知我 进行注册，即可每周接收产品信息更改摘要。有关更改的详细信息，请查看任何已修订文档中包含的修订历史记录。

12.3 社区资源

下列链接提供到 TI 社区资源的连接。链接的内容由各个分销商“按照原样”提供。这些内容并不构成 TI 技术规范，并且不一定反映 TI 的观点；请参阅 TI 的《使用条款》。

TI E2E™ 在线社区 TI 的工程师对工程师 (E2E) 社区。此社区的创建目的在于促进工程师之间的协作。在 e2e.ti.com 中，您可以咨询问题、分享知识、拓展思路并与同行工程师一道帮助解决问题。

设计支持 TI 参考设计支持 可帮助您快速查找有帮助的 E2E 论坛、设计支持工具以及技术支持的联系信息。

12.4 商标

E2E is a trademark of Texas Instruments.

All other trademarks are the property of their respective owners.

12.5 静电放电警告



这些装置包含有限的内置 ESD 保护。存储或装卸时，应将导线一起截短或将装置放置于导电泡棉中，以防止 MOS 门极遭受静电损伤。

12.6 术语表

SLYZ022 — TI 术语表。

这份术语表列出并解释术语、缩写和定义。

13 机械、封装和可订购信息

以下页面包含机械、封装和可订购信息。这些信息是指定器件的最新可用数据。数据如有变更，恕不另行通知，且不会对此文档进行修订。如需获取此产品说明书的浏览器版本，请查阅左侧的导航栏。

PACKAGING INFORMATION

Orderable part number	Status (1)	Material type (2)	Package Pins	Package qty Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
74CBTLV3257PWRG4	Active	Production	TSSOP (PW) 16	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	CL257
SN74CBTLV3257D	Obsolete	Production	SOIC (D) 16	-	-	Call TI	Call TI	-40 to 85	CBTLV3257
SN74CBTLV3257DBQR	Active	Production	SSOP (DBQ) 16	2500 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	CL257
SN74CBTLV3257DGVR	Active	Production	TVSOP (DGV) 16	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	CL257
SN74CBTLV3257DR	Active	Production	SOIC (D) 16	2500 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	CBTLV3257
SN74CBTLV3257PW	Obsolete	Production	TSSOP (PW) 16	-	-	Call TI	Call TI	-40 to 85	CL257
SN74CBTLV3257PWR	Active	Production	TSSOP (PW) 16	2000 LARGE T&R	Yes	NIPDAU SN	Level-1-260C-UNLIM	-40 to 85	CL257
SN74CBTLV3257RGYR	Active	Production	VQFN (RGY) 16	3000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	CL257
SN74CBTLV3257RSVR	Active	Production	UQFN (RSV) 16	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	ZTR

⁽¹⁾ **Status:** For more details on status, see our [product life cycle](#).

⁽²⁾ **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

⁽³⁾ **RoHS values:** Yes, No, RoHS Exempt. See the [TI RoHS Statement](#) for additional information and value definition.

⁽⁴⁾ **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

⁽⁵⁾ **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

⁽⁶⁾ **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "-" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and

continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

OTHER QUALIFIED VERSIONS OF SN74CBTLV3257 :

- Enhanced Product : [SN74CBTLV3257-EP](#)

NOTE: Qualified Version Definitions:

- Enhanced Product - Supports Defense, Aerospace and Medical Applications

TAPE AND REEL INFORMATION



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
74CBTLV3257PWRG4	TSSOP	PW	16	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
SN74CBTLV3257DBQR	SSOP	DBQ	16	2500	330.0	12.5	6.4	5.2	2.1	8.0	12.0	Q1
SN74CBTLV3257DGVR	TVSOP	DGV	16	2000	330.0	12.4	6.8	4.0	1.6	8.0	12.0	Q1
SN74CBTLV3257DR	SOIC	D	16	2500	330.0	16.4	6.5	10.3	2.1	8.0	16.0	Q1
SN74CBTLV3257PWR	TSSOP	PW	16	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
SN74CBTLV3257RGYR	VQFN	RGY	16	3000	330.0	12.4	3.8	4.3	1.5	8.0	12.0	Q1
SN74CBTLV3257RSVR	UQFN	RSV	16	3000	180.0	13.2	2.1	2.9	0.75	4.0	12.0	Q1

TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
74CBTLV3257PWRG4	TSSOP	PW	16	2000	367.0	367.0	35.0
SN74CBTLV3257DBQR	SSOP	DBQ	16	2500	353.0	353.0	32.0
SN74CBTLV3257DGVR	TVSOP	DGV	16	2000	367.0	367.0	35.0
SN74CBTLV3257DR	SOIC	D	16	2500	353.0	353.0	32.0
SN74CBTLV3257PWR	TSSOP	PW	16	2000	367.0	367.0	35.0
SN74CBTLV3257RGYR	VQFN	RGY	16	3000	367.0	367.0	35.0
SN74CBTLV3257RSVR	UQFN	RSV	16	3000	180.0	180.0	30.0

D (R-PDSO-G16)

PLASTIC SMALL OUTLINE



4040047-6/M 06/11

- NOTES:
- A. All linear dimensions are in inches (millimeters).
 - B. This drawing is subject to change without notice.
 - C. Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
 - D. Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
 - E. Reference JEDEC MS-012 variation AC.



4220204/A 02/2017

NOTES:

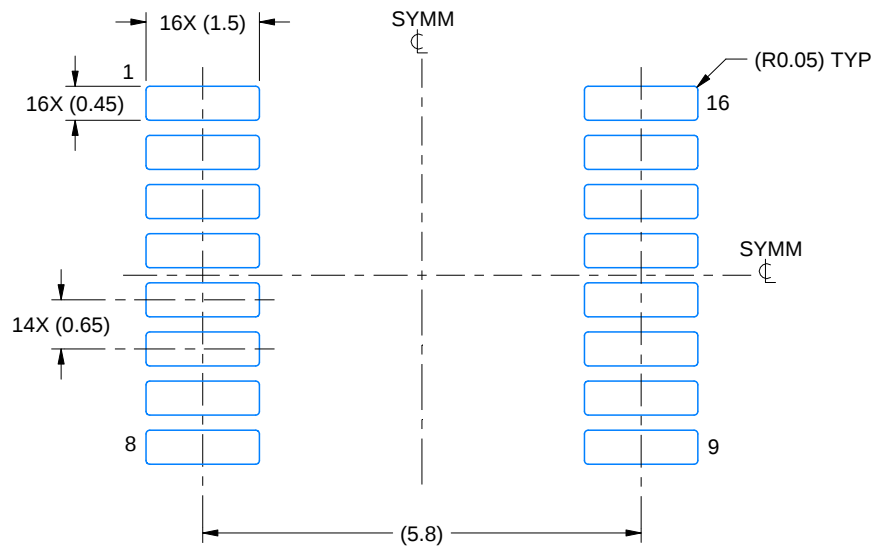
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
5. Reference JEDEC registration MO-153.

EXAMPLE BOARD LAYOUT

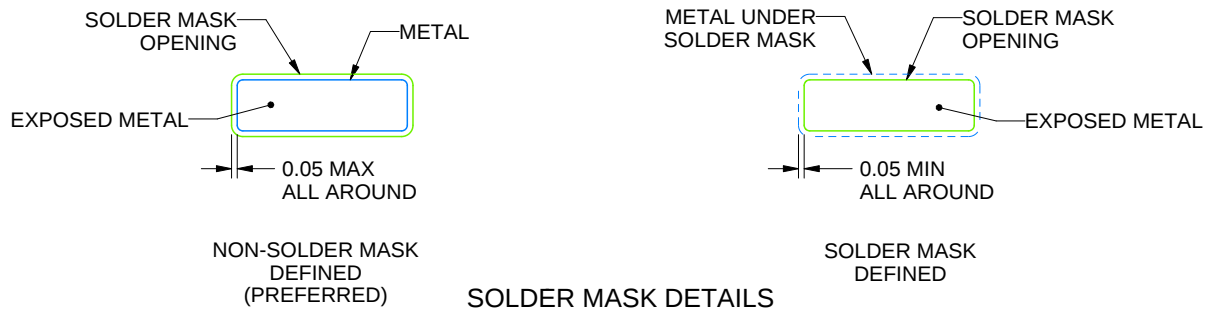
PW0016A

TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE: 10X



4220204/A 02/2017

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

PW0016A

TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE: 10X

4220204/A 02/2017

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

GENERIC PACKAGE VIEW

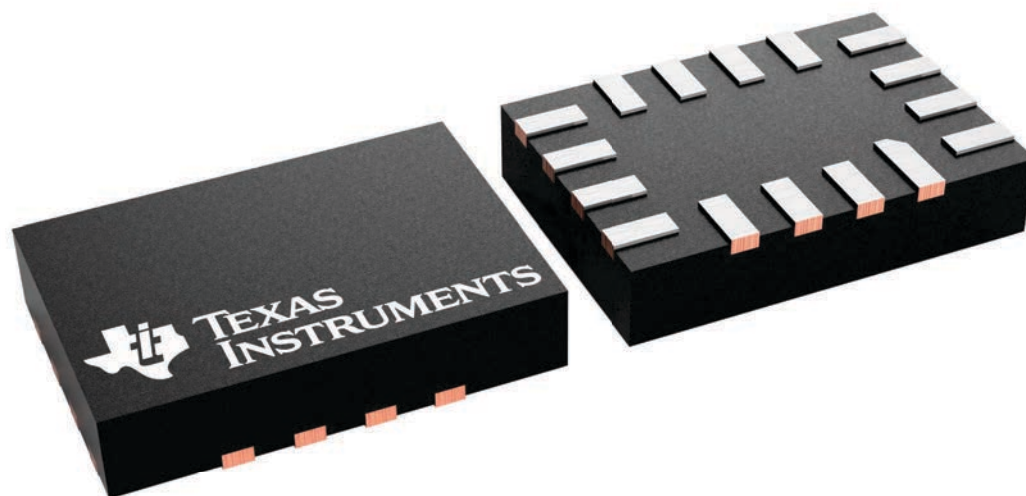
RSV 16

UQFN - 0.55 mm max height

1.8 x 2.6, 0.4 mm pitch

ULTRA THIN QUAD FLATPACK - NO LEAD

This image is a representation of the package family, actual package may vary.
Refer to the product data sheet for package details.



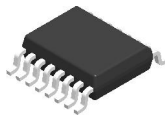
DGV (R-PDSO-G**)

PLASTIC SMALL-OUTLINE

24 PINS SHOWN



- NOTES: A. All linear dimensions are in millimeters.
 B. This drawing is subject to change without notice.
 C. Body dimensions do not include mold flash or protrusion, not to exceed 0,15 per side.
 D. Falls within JEDEC: 24/48 Pins – MO-153
 14/16/20/56 Pins – MO-194

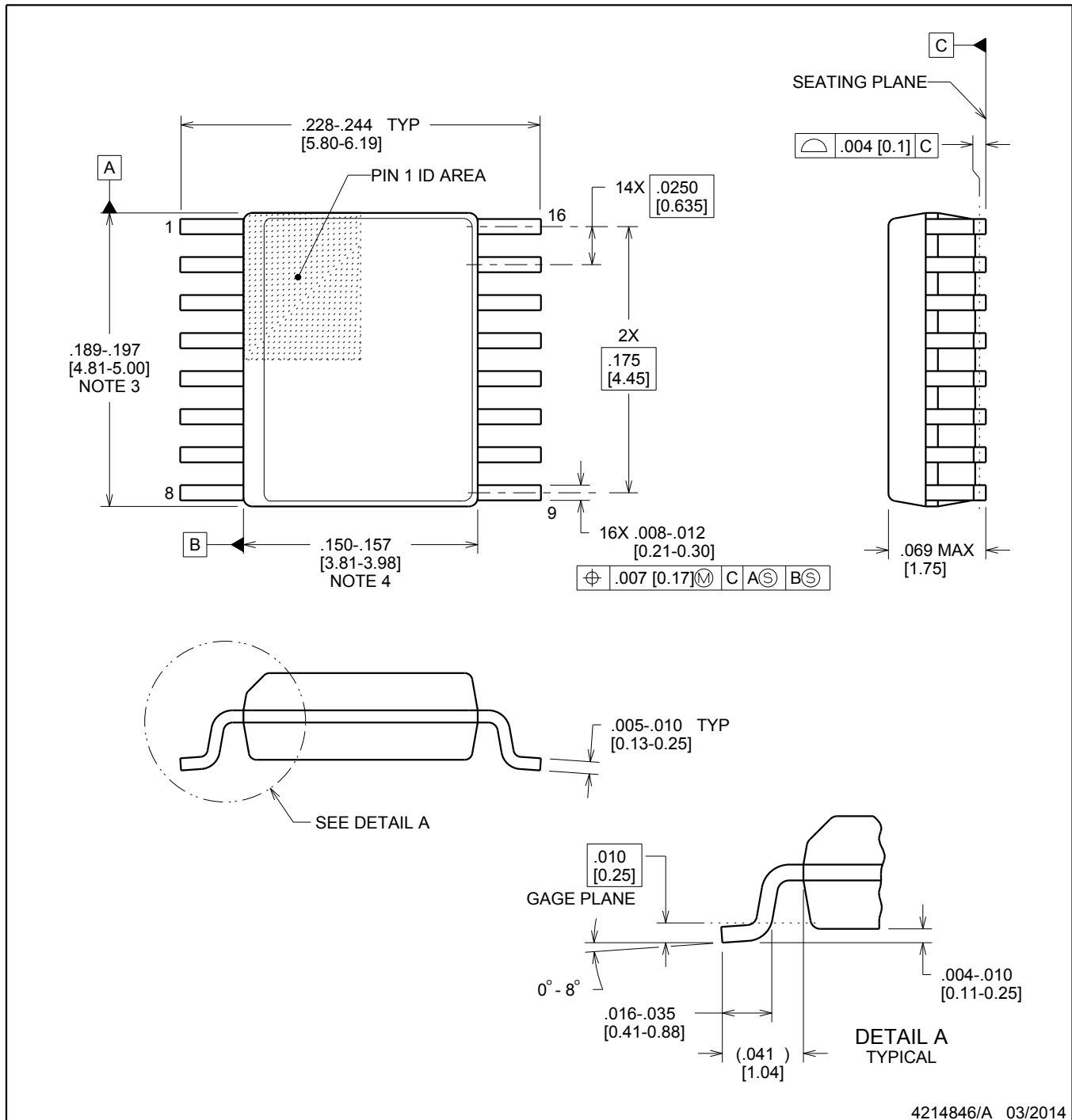


DBQ0016A

PACKAGE OUTLINE

SSOP - 1.75 mm max height

SHRINK SMALL-OUTLINE PACKAGE



4214846/A 03/2014

NOTES:

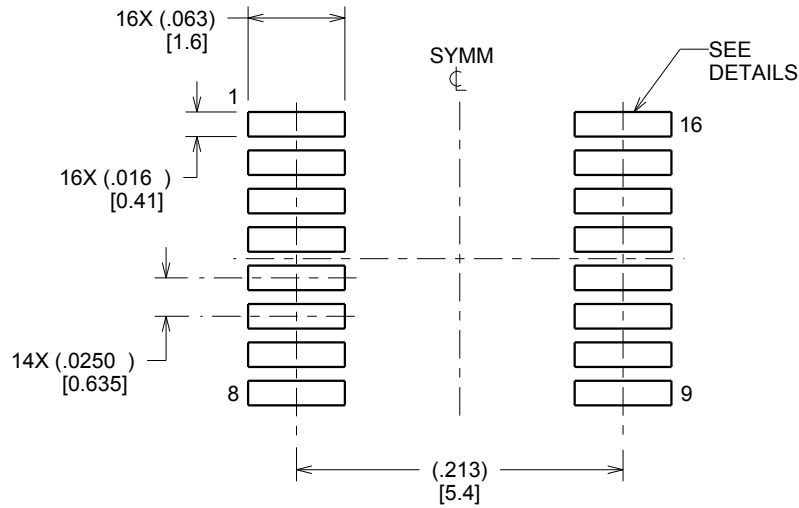
- Linear dimensions are in inches [millimeters]. Dimensions in parenthesis are for reference only. Controlling dimensions are in inches. Dimensioning and tolerancing per ASME Y14.5M.
- This drawing is subject to change without notice.
- This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed .006 inch, per side.
- This dimension does not include interlead flash.
- Reference JEDEC registration MO-137, variation AB.

EXAMPLE BOARD LAYOUT

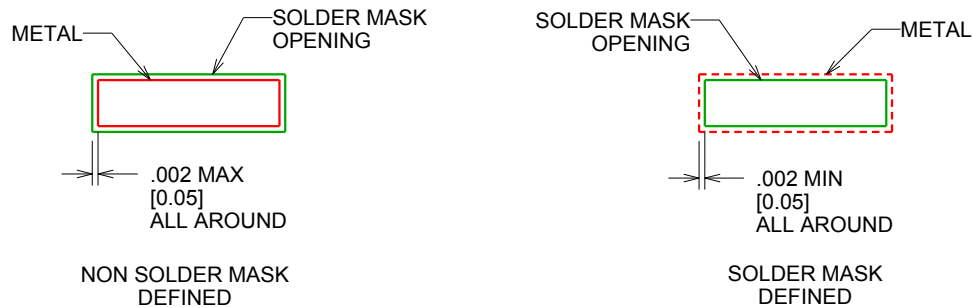
DBQ0016A

SSOP - 1.75 mm max height

SHRINK SMALL-OUTLINE PACKAGE



LAND PATTERN EXAMPLE
SCALE:8X



SOLDER MASK DETAILS

4214846/A 03/2014

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

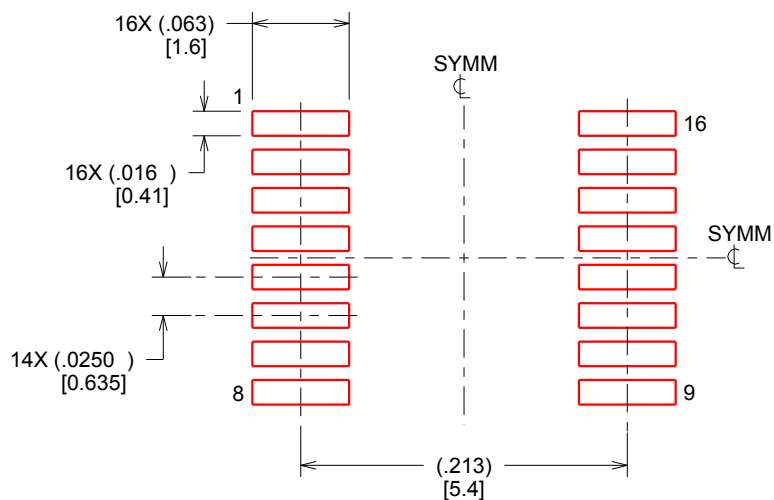
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

DBQ0016A

SSOP - 1.75 mm max height

SHRINK SMALL-OUTLINE PACKAGE



SOLDER PASTE EXAMPLE
BASED ON .005 INCH [0.127 MM] THICK STENCIL
SCALE:8X

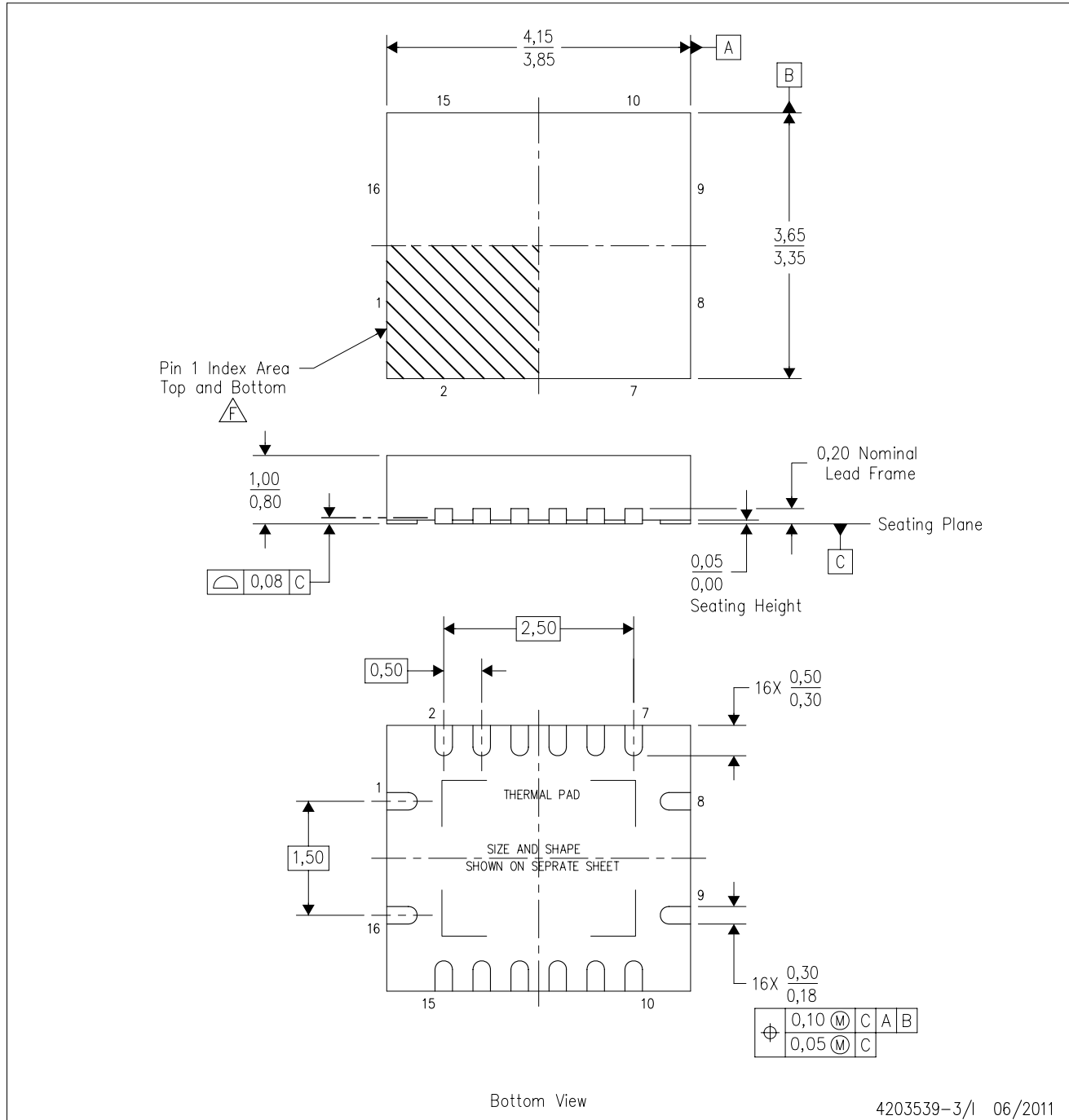
4214846/A 03/2014

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

RGY (R-PVQFN-N16)

PLASTIC QUAD FLATPACK NO-LEAD



4203539-3/I 06/2011

- NOTES:
- All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M-1994.
 - This drawing is subject to change without notice.
 - QFN (Quad Flatpack No-Lead) package configuration.
 - The package thermal pad must be soldered to the board for thermal and mechanical performance.
 - See the additional figure in the Product Data Sheet for details regarding the exposed thermal pad features and dimensions.
- F** Pin 1 identifiers are located on both top and bottom of the package and within the zone indicated. The Pin 1 identifiers are either a molded, marked, or metal feature.
- Package complies to JEDEC MO-241 variation BA.

RGY (R-PVQFN-N16)

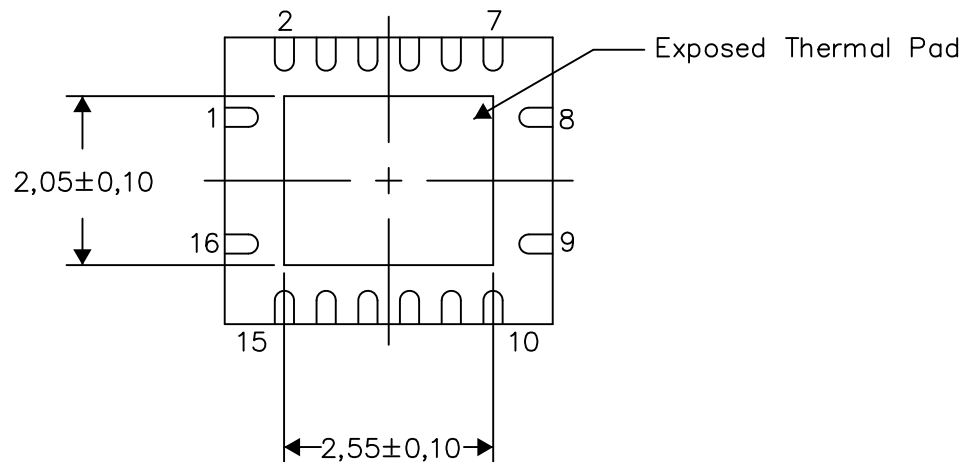
PLASTIC QUAD FLATPACK NO-LEAD

THERMAL INFORMATION

This package incorporates an exposed thermal pad that is designed to be attached directly to an external heatsink. The thermal pad must be soldered directly to the printed circuit board (PCB). After soldering, the PCB can be used as a heatsink. In addition, through the use of thermal vias, the thermal pad can be attached directly to the appropriate copper plane shown in the electrical schematic for the device, or alternatively, can be attached to a special heatsink structure designed into the PCB. This design optimizes the heat transfer from the integrated circuit (IC).

For information on the Quad Flatpack No-Lead (QFN) package and its advantages, refer to Application Report, QFN/SON PCB Attachment, Texas Instruments Literature No. SLUA271. This document is available at www.ti.com.

The exposed thermal pad dimensions for this package are shown in the following illustration.

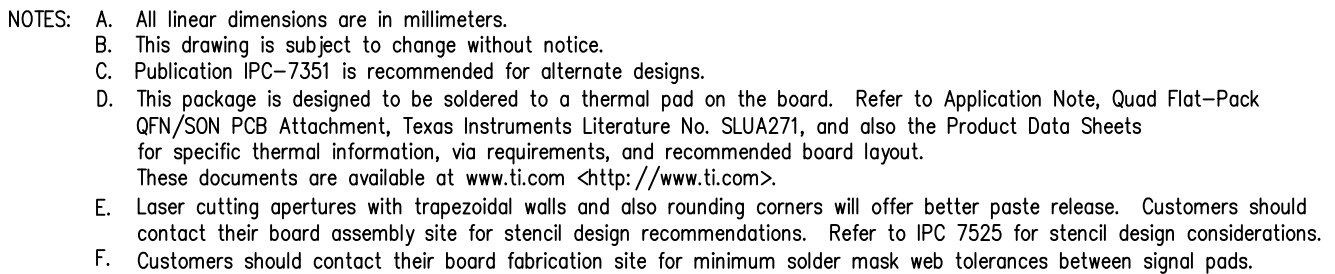


Bottom View

Exposed Thermal Pad Dimensions

4206353-3/P 03/14

NOTE: All linear dimensions are in millimeters



重要通知和免责声明

TI“按原样”提供技术和可靠性数据（包括数据表）、设计资源（包括参考设计）、应用或其他设计建议、网络工具、安全信息和其他资源，不保证没有瑕疵且不做任何明示或暗示的担保，包括但不限于对适销性、某特定用途方面的适用性或不侵犯任何第三方知识产权的暗示担保。

这些资源可供使用 TI 产品进行设计的熟练开发人员使用。您将自行承担以下全部责任：(1) 针对您的应用选择合适的 TI 产品，(2) 设计、验证并测试您的应用，(3) 确保您的应用满足相应标准以及任何其他功能安全、信息安全、监管或其他要求。

这些资源如有变更，恕不另行通知。TI 授权您仅可将这些资源用于研发本资源所述的 TI 产品的相关应用。严禁以其他方式对这些资源进行复制或展示。您无权使用任何其他 TI 知识产权或任何第三方知识产权。您应全额赔偿因在这些资源的使用中对 TI 及其代表造成的任何索赔、损害、成本、损失和债务，TI 对此概不负责。

TI 提供的产品受 [TI 的销售条款](#) 或 [ti.com](#) 上其他适用条款/TI 产品随附的其他适用条款的约束。TI 提供这些资源并不会扩展或以其他方式更改 TI 针对 TI 产品发布的适用的担保或担保免责声明。

TI 反对并拒绝您可能提出的任何其他或不同的条款。

邮寄地址：Texas Instruments, Post Office Box 655303, Dallas, Texas 75265
版权所有 © 2025，德州仪器 (TI) 公司